Serial No. 10/808,059 Attorney Docket No. 400.285US01
Title: NROM MEMORY DEVICE WITH HIGH-PERMITTIVITY GATE DIELECTRIC FORMED BY THE

LOW TEMPERATURE OXIDIZATION OF METALS

## **AMENDMENTS TO THE SPECIFICATION**

Please replace the original paragraph 25 with this replacement paragraph 25:

[0025] Embodiments of this category of oxide – nitride – high-k dielectric layers nanolaminates include: oxide –  $\frac{\text{oxide}}{\text{oxide}}$  –  $\frac{\text{nitride}}{\text{oxide}}$  –  $\frac{\text{Al}_2\text{O}_3}{\text{oxide}}$  (where the Al is oxidized to form the  $\frac{\text{Al}_2\text{O}_3}{\text{oxide}}$ ), oxide –  $\frac{\text{oxide}}{\text{oxide}}$  –  $\frac{\text{nitride}}{\text{oxidized}}$  –  $\frac{\text{Al}_2\text{O}_3}{\text{oxide}}$ . Alternate embodiments may include other dielectric materials.